

The **SM08010-42L** is a solid state GaAs FET amplifier designed for the Cellular/Global Standard for Mobile (GSM) market. This amplifier operates from 800 – 1000 MHz, provides 50 dB of gain, ± 0.5 dB gain flatness over the full band, and +42 dBm of output power at its 1 dB compression point. The output third order intercept point is +58 dBm. Its compact size and high linearity make it ideally suited for systems using CDMA or TDMA standards.



Features

- Mis-Match Protected
- Temperature compensation
- Single Power Supply
- Over/Reverse Voltage Protection
- Thermal Protection with Auto Reset

Options

- Logic On/Off Control
- Forward Power Detector
- Heatsink

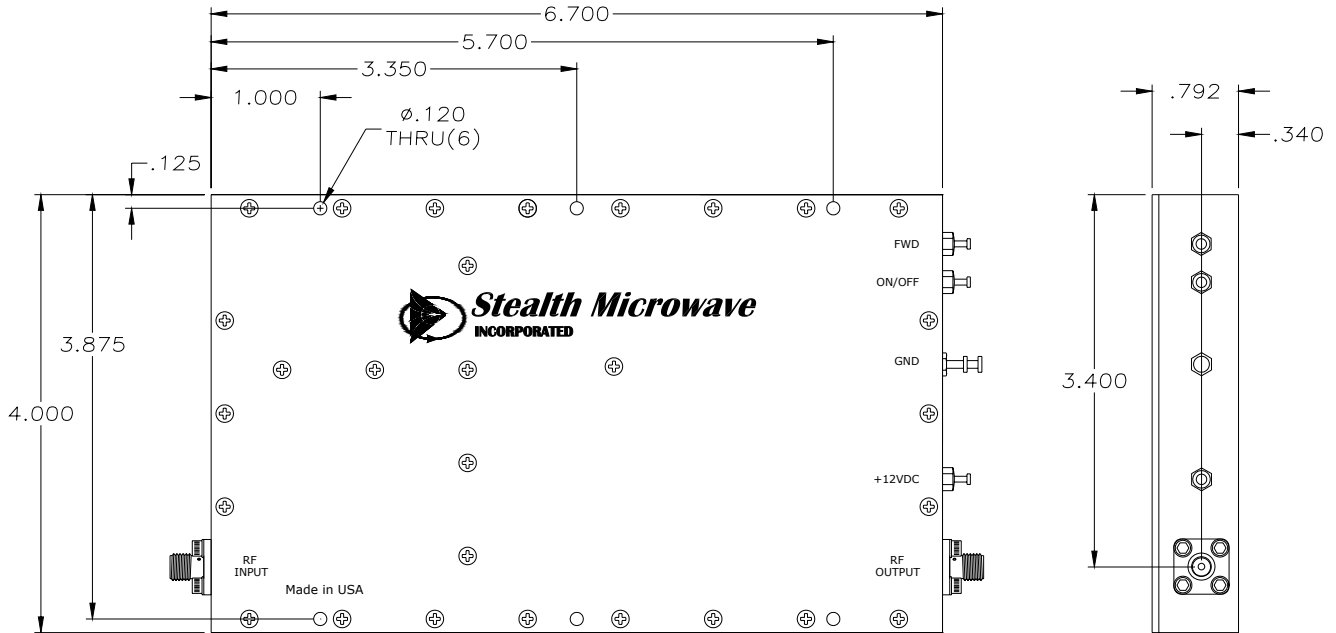
Configurations

- Module
- 19" Rack

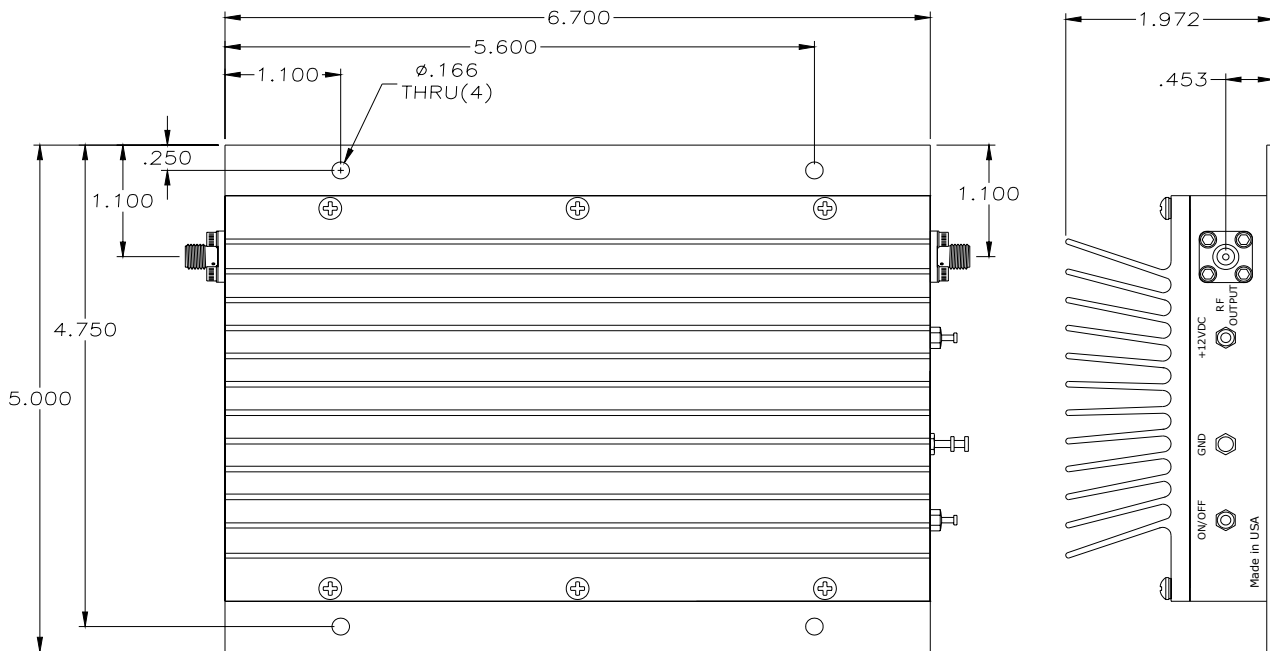
Parameter	Specification
Frequency Range	800 - 1000 MHz
Pout (P1dB)	+ 41 dBm
Third Order Intercept Point	+ 58 dBm (typ.)
Linear Gain	50 dB \pm 1 dB
Gain Flatness over Full Band	$\pm .5$ dB
Input/Output Return Loss	-14 dB / -16 dB
DC Input Voltage	+ 12 Volts
DC Input Current	6.0 Amperes (Varies per application)
Mechanical Dimensions Without Heatsink	6.7 x 4.0 x 0.8 Inches
RF Connectors	SMA Female
Operating Temperature	0°C to +85°C
Operating Humidity	95% Non-condensing
Operating Altitude	Up to 10,000 feet above Sea Level

Specifications subject to change without notice

DIMENSIONS IN INCHES



HEATSINK OPTION



Pin	Description	Values
RF Input	Input Connector (SMA Female)	- 8 dBm, typical, -6 dBm max
RF OUT	Output Connector (SMA Female)	+41 dBm @P1dB
FWD	Forward Power Detection	2.5V @ +35 dBm Pout
GND	Ground Turret	---
+12VDC	DC Input Voltage	+ 12 Volts @ 6.0 Amperes (typ.)
ON/OFF	TTL Logic On/Off	0 Volts = Off, + 5 Volts = On